MJE51T





isc Silicon NPN Power Transistor

DESCRIPTION

- · Collector-Emitter Sustaining Voltage-
 - : V_{CEO(SUS)} = 250V(Min)
- ·Minimum Lot-to-Lot variations for robust device performance and reliable operation

PIN 1. BASE 2.COLLECTOR 3. BMITTER TO-220C package

APPLICATIONS

• Designed for high voltage inverters, switching regulators and line operated amplifier applications. Especially well suited for switching power supply applications

ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT	
V _{CBO}	Collector-Base Voltage	350	V	
VCEO	Collector-Emitter Voltage	250	V	
V _{EBO}	Emitter-Base Voltage	V		
Ic	Collector Current-Continuous 5		Α	
Ісм	Collector Current-Peak	10	Α	
l _Β	Base Current-Continuous	e Current-Continuous 2		
Pc	Collector Power Dissipation @ T _C =25°C	80	W	
TJ	Junction Temperature	150	$^{\circ}$	
T _{stg}	Storage Temperature Range -65~150		$^{\circ}$ C	

mm DIM MIN MAX A 15.50 15.90 10.20 4.20 D 0.70 3.40 3.70 G 4.98 Н 2.68 0.44 12.80 1.20 2.70 Q 2.30 1.29 1.35 6.65 6.45 8.66

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R _{th j-c}	Thermal Resistance,Junction to Case	1.56	°C/W



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ELECTRICAL CHARACTERISTICS

Tc=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT			
V _{CEO(SUS)}	Collector-Emitter Sustaining Voltage	I _C = 25mA; I _B = 0	250			V			
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 5A; I _B = 2A			2.0	V			
V _{BE(on)}	Base-Emitter On Voltage	I _C = 5A ; V _{CE} = 10V			2.0	V			
I _{CEO}	Collector Cutoff Current	V _{CE} = 150V; I _B =0			1.0	mA			
Ices	Collector Cutoff Current	V _{CE} = 350V; V _{BE} = 0			1.0	mA			
I _{EBO}	Emitter Cutoff Current	V _{EB} = 5V; I _C =0			1.0	mA			
h _{FE-1}	DC Current Gain	I _C = 0.3A ; V _{CE} = 10V	30						
h _{FE-2}	DC Current Gain	I _C = 5A; V _{CE} = 10V	5						
Сов	Output Capacitance	I _E = 0 ; V _{CB} = 10V; f _{test} =0.1MHz		150		pF			
Switching times									
t _{on}	Turn-On Time	I _C = 2.5A , I _{B1} = -I _{B2} = 0.5A		0.5		μs			
t _{off}	Turn-Off Time	V _{BE(off)} = 5V; V _{CC} = 125V		2.0		μS			

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